

In response to the Advisory Action of February, 2003, please amend the above-identified application as follows:

In the Claims:

Please amend claims 11 - 17 as follows:

11. (THRICE AMENDED) A method for removing cohesive coatings from a plurality of substrates having dense submicron topography containing prominent sidewalls, comprising the steps of:

placing a quartz gas distribution plate, connected to a pressure regulated gas supply, in an open tank containing a liquid chemical; submerging and placing a substrate carrier, containing a plurality of substrates, on said quartz gas distribution plate so that said substrates are aligned and in a vertical position relative to said quartz gas distribution plate;

intermittently changing a pressure of said regulated gas supply for generating a turbulent vertical agitation, said distribution plate directs gas bubbles between and parallel to each surface of said substrates aligned thereabove, said turbulent vertical agitation providing a chemical-mechanical scrubbing;

removing said substrate carrier from said chemical liquid.

12. (THRICE AMENDED) The method according to claim 11 wherein said quartz gas distribution plate having distribution means for generating an array of gas bubbles, each row of said array corresponding to a substrate position

20 of said substrate carrier.

13. (THRICE AMENDED) The method according to claim 11 wherein said pressure regulated gas supply is nitrogen gas.

25 14. (THRICE AMENDED) The method according to claim 11 wherein using a quartz gas distribution plate is compatible with aggressive chemicals for removing cohesive residues in metal sidewalls that are coated with polymer.

30 15. (THRICE AMENDED) A method for stripping cohesive photoresist from a plurality of semiconductor wafers having dense submicron topography containing prominent sidewalls, comprising the steps of:

horizontally placing a quartz gas distribution plate, connected to a pressure regulated gas supply, in an open tank containing a photoresist stripping chemical;

35 submerging and placing a wafer cassette containing a plurality of wafers on said quartz gas distribution plate so that said wafers are aligned and in a vertical position relative to said quartz gas distribution plate;
intermittently changing said pressure of said pressure regulated gas supply for generating a turbulent vertical agitation, said distribution plate directs
40 gas bubbles between and parallel to each surface of said wafers aligned thereabove, said turbulent vertical agitation providing a chemical-mechanical scrubbing;

Sub D2
45 removing said wafer cassette from said photoresist stripping liquid.

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16. (THRICE AMENDED) The method according to claim 11 wherein said quartz gas distribution plate having distribution means for generating an array of gas bubbles, each row of said array corresponding to a wafer position of said wafer cassette.

50 17. (THRICE AMENDED) The method according to claim 11 wherein said pressure regulated gas supply is nitrogen gas.

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55 18. (THRICE AMENDED) The method according to claim 11 wherein using a quartz gas distribution plate is compatible with aggressive chemicals for removing cohesive residues in metal sidewalls that are coated with cohesive photoresist.

REMARKS/ARGUMENTS

Claims 11 - 18 have been amended. No new matter has been added.

Claims 11 - 18 have been rewritten to further clarify the process while removing any claimed reference to the apparatus in response to the Examiner's kind suggestions.